

Electron transport in semiconducting SnO₂: Intentional bulk donors and acceptors, the interface, and the surface – CORRIGENDUM

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REFERENCE

1. O. Bierwagen, T. Nagata, M.E. White, M.-Y. Tsai, J.S. Speck: Electron transport in semiconducting SnO₂: Intentional bulk donors and acceptors, the interface, and the surface. *J. Mater. Res.* **27**(17), 2232–2236 (2012).